



## SSCU0504NP40GSA

### N and P-Channel Enhancement Mode Power MOSFET

#### ➤ Features

##### N-Channel

$V_{DS}$	$V_{GS}$	$R_{DS(ON)}$ Typ.	$I_D$
40V	$\pm 20V$	40m $\Omega$ @10V	5A
		55m $\Omega$ @4.5V	

##### P-Channel

$V_{DS}$	$V_{GS}$	$R_{DS(ON)}$ Typ.	$I_D$
-40V	$\pm 20V$	70m $\Omega$ @-10V	-4A
		108m $\Omega$ @-4.5V	

#### ➤ Description

The SSCU0504NP40GSA uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

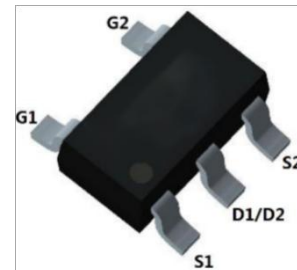
#### ➤ Applications

- Power supply
- Switching circuits
- DC-DC Converters

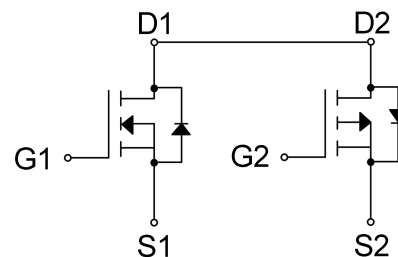
#### ➤ Ordering Information

Device	Package	Shipping
SSCU0504NP40GSA	SOT23-5L	3000/Reel

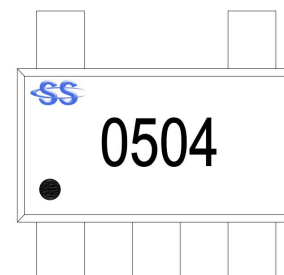
#### ➤ Pin configuration



**SOT23-5L (Top View)**



**Pin Configuration**



**Marking**

**➤ Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-to-Source Voltage		$V_{\text{DSS}}$	40	-40	V
Gate-to-Source Voltage		$V_{\text{GSS}}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current <sup>a</sup>	$T_A = 25^{\circ}\text{C}$	$I_{\text{D}}$	5	-4	A
	$T_A = 100^{\circ}\text{C}$		2.6	-2	A
Pulsed Drain Current <sup>b</sup>		$I_{\text{DM}}$	20	-16	A
Power Dissipation <sup>a</sup>		$I_{\text{DSM}}$	5	-3.7	A
Power Dissipation <sup>c</sup>	$T_A = 25^{\circ}\text{C}$	$P_{\text{D}}$	1.6	1.6	W
	$T_A = 100^{\circ}\text{C}$		0.6	0.6	W
Operation junction temperature		$T_{\text{J}}$	-55 to 150	-55 to 150	$^{\circ}\text{C}$
Storage temperature range		$T_{\text{STG}}$	-55 to 150	-55 to 150	$^{\circ}\text{C}$

**➤ Thermal Resistance Ratings ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Symbol	Parameter	N-Channel	P-Channel	Unit
$R_{\theta\text{JA}}$	Junction-to-Case Thermal Resistance	80	80	$^{\circ}\text{C}/\text{W}$

Note:

- The value of  $R_{\theta\text{JA}}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation  $P_{\text{D}}$  is based on  $T_{\text{J(MAX)}}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.



# SSCU0504NP40GSA

## ➤ N-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250uA	40			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250uA	1	1.5	2.5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4A		40	55	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3A		55	78	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V			1	μA
Gate-Source Leak Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A		0.8	1.3	V
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz		450		pF
Output Capacitance	C <sub>OSS</sub>			39		
Reverse Transfer Capacitance	C <sub>RSS</sub>			34		
Total Gate Charge	Q <sub>G</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 20V, I <sub>D</sub> = 2A		8		nC
Gate to Source Charge	Q <sub>GS</sub>			1.2		
Gate to Drain Charge	Q <sub>GD</sub>			2.2		
Turn-on Delay Time	T <sub>D(ON)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 20V, I <sub>D</sub> = 2A, R <sub>G</sub> = 3Ω		10		ns
Rise Time	T <sub>r</sub>			12		
Turn-off Delay Time	T <sub>D(OFF)</sub>			16		
Fall Time	T <sub>f</sub>			10		



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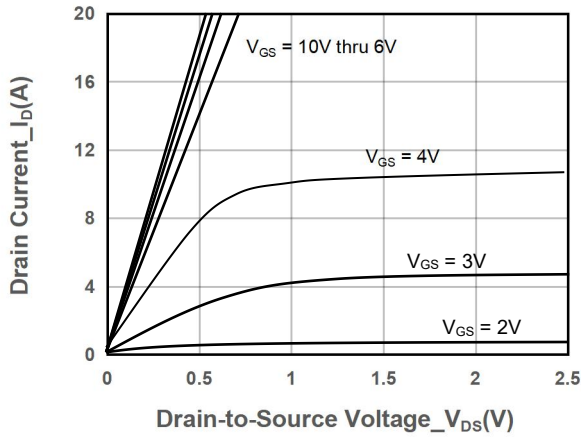
## ➤ P-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-40			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250uA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3A		70	95	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2A		108	140	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V			-1	μA
Gate-Source Leak Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A		-0.8	-1.3	V
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V, f = 1MHz		478		pF
Output Capacitance	C <sub>OSS</sub>			45		
Reverse Transfer Capacitance	C <sub>RSS</sub>			36		
Total Gate Charge	Q <sub>G</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -20V, I <sub>D</sub> = -3A		6.2		nC
Gate to Source Charge	Q <sub>GS</sub>			1.5		
Gate to Drain Charge	Q <sub>GD</sub>			1.5		
Turn-on Delay Time	T <sub>D(ON)</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -20V, I <sub>D</sub> = -1A, R <sub>G</sub> = 3Ω,		11		ns
Rise Time	T <sub>r</sub>			5.6		
Turn-off Delay Time	T <sub>D(OFF)</sub>			46		
Fall Time	T <sub>f</sub>			9		

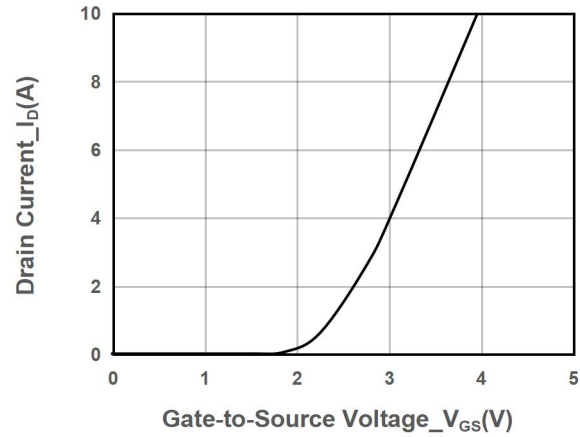


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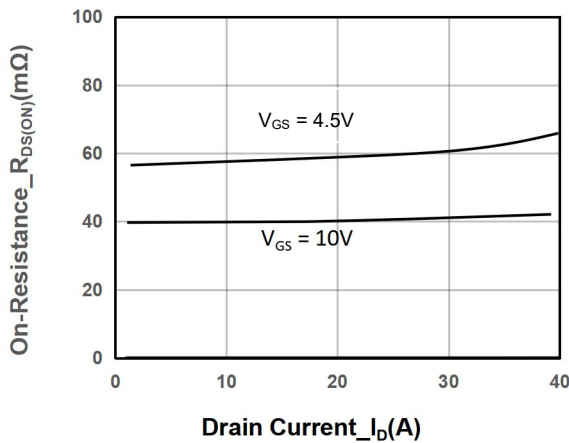
## ➤ N-Channel Typical Performance Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)



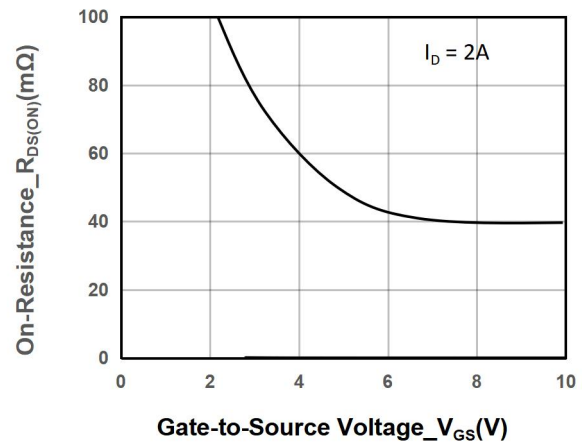
Output Characteristics



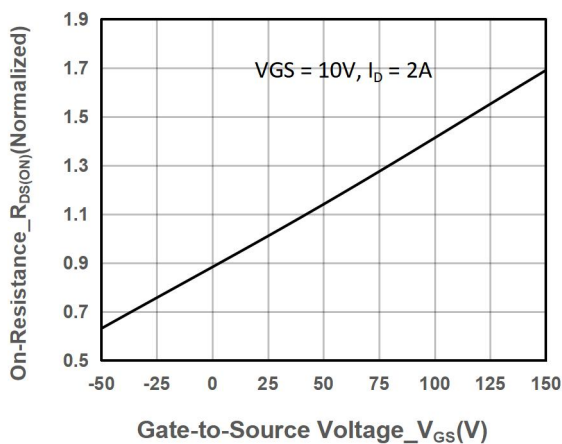
Transfer Characteristics



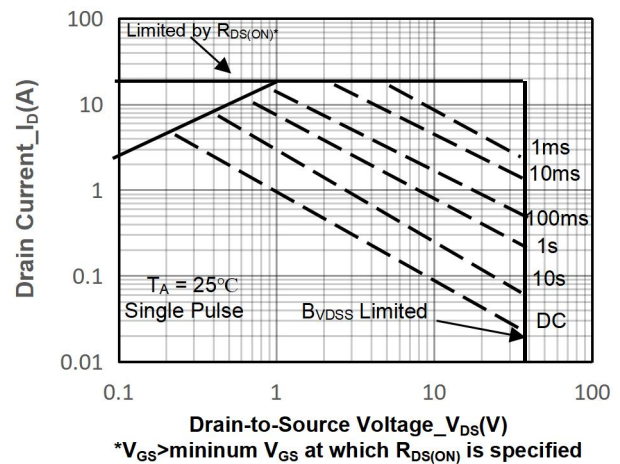
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature

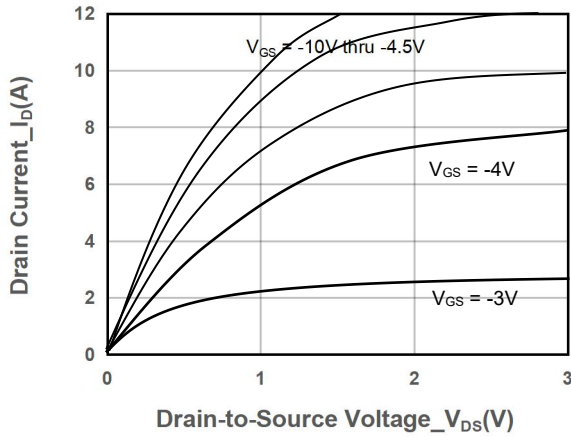


Safe Operating Area vs. Junction-to-Ambient

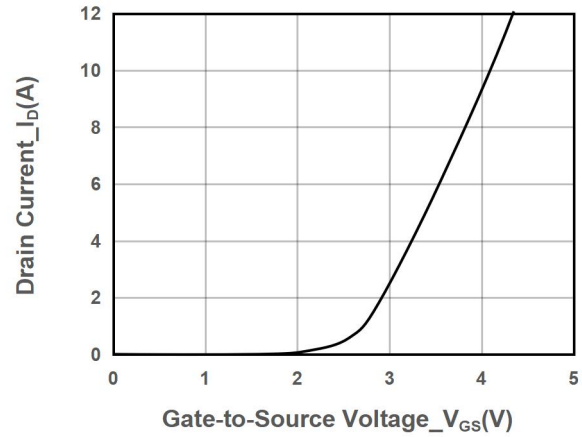


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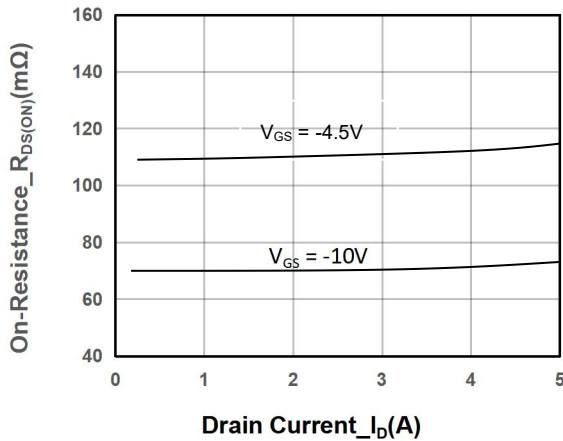
## ➤ P-Channel Typical Performance Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)



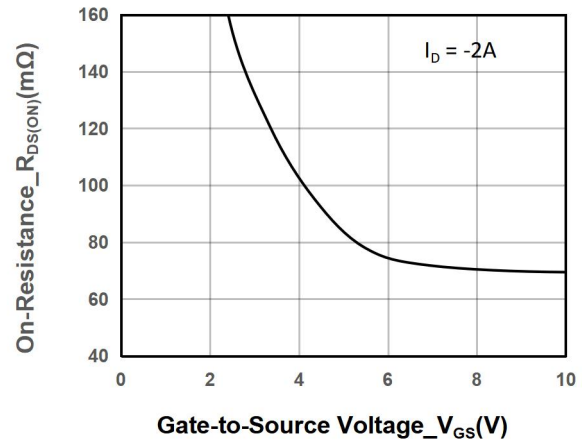
Output Characteristics



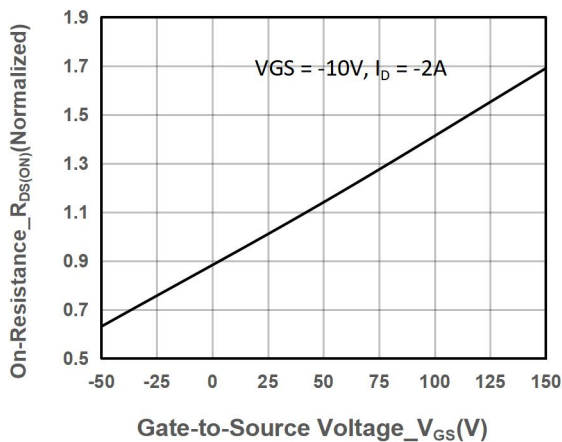
Transfer Characteristics



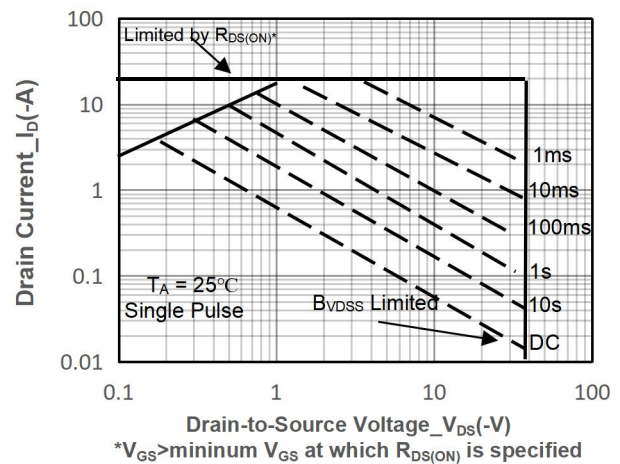
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage

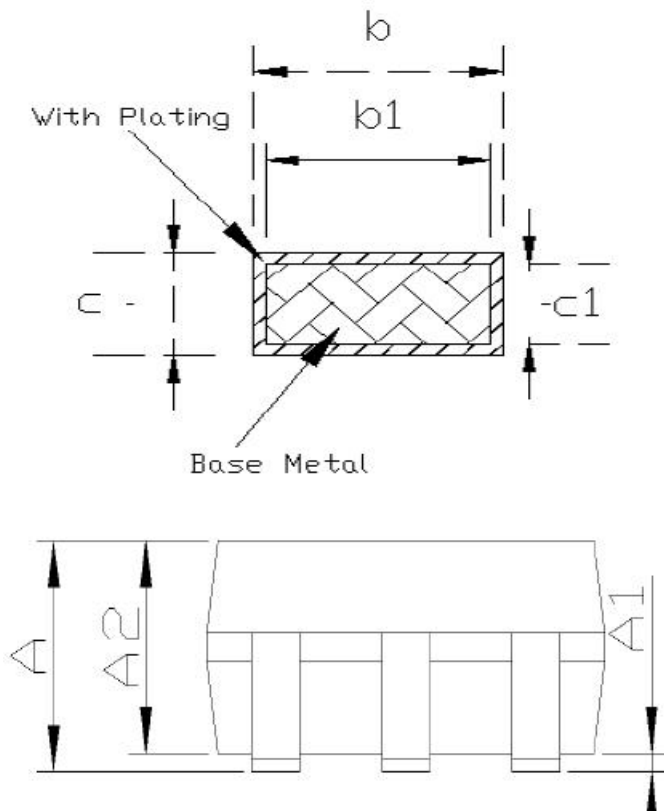


On-Resistance vs. Junction Temperature

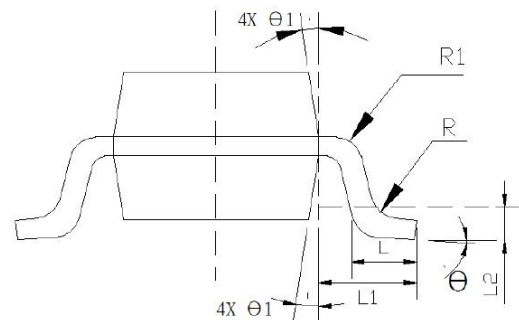
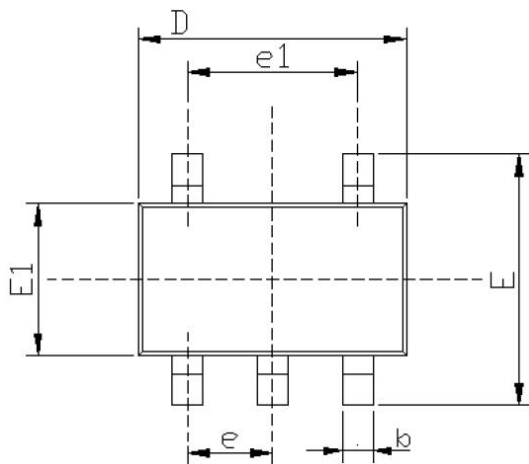


Safe Operating Area vs. Junction-to-Ambient

## ➤ Package Information



Common Dimensions (Units of Measure=Millimeter)			
SYMBOL	MINIMUM	NOMINAL	MAXIMUM
A	-	-	1.35
A1	0	-	0.15
A2	1.00	1.10	1.20
b	0.35	-	0.45
b1	0.32	-	0.38
c	0.14	-	0.20
c1	0.14	0.15	0.16
D	2.82	2.92	3.02
E	2.60	2.80	3.00
E1	1.526	1.626	1.726
e	0.90	0.95	1.00
e1	1.80	1.90	2.00
L	0.35	0.45	0.60
L1	0.6 REF		
L2	0.25 REF		
R	0.10	-	-
R1	0.10	-	0.25
θ	0°	4°	8°
θ 1	5°	10°	15°





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